

# n-channel JFETs designed for . . .



## Performance Curves NS See Section 4

### ■ Audio and Sub-Audio Amplifiers

#### BENEFITS

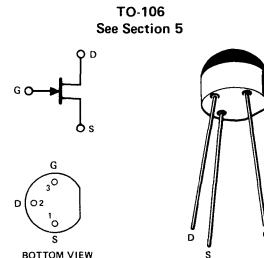
- Ultra Low Noise

$\overline{e_n} = 8 \text{ nV}/\sqrt{\text{Hz}}$  Typical at 10 Hz

$\overline{e_n} = 2 \text{ nV}/\sqrt{\text{Hz}}$  Typical at 1 kHz

#### ABSOLUTE MAXIMUM RATINGS (25°C)

Gate-Drain or Gate-Source Voltage (Note 1) . . . . .	-40 V
Gate Current . . . . .	50 mA
Total Device Dissipation . . . . .	350 mW
(25°C Free-Air Temperature) . . . . .	3.5 mW/°C
Power Derating (to +125°C) . . . . .	
Storage Temperature Range . . . . .	-55 to +125°C
Operating Temperature Range . . . . .	-55 to +125°C
Lead Temperature (1/16" from case for 10 seconds) . . . . .	300°C



#### ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

Characteristic	E230			E231			E232			Unit	Test Conditions
	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max		
I <sub>GSS</sub>				-250			-250			-250	pA
V <sub>GSOFF</sub>	-1	-3	-2	-5	-4		-6			V	V <sub>DS</sub> = 20 V, I <sub>D</sub> = 1 μA
BV <sub>GSS</sub>	-40			-40			-40				V <sub>DS</sub> = 0, I <sub>G</sub> = -1 μA
I <sub>DSS</sub>	0.7	3	2	6	5		10			mA	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0
I <sub>G</sub>		-10		-10			-10			pA	V <sub>DG</sub> = 10 V, I <sub>D</sub> = 0.5 mA
g <sub>fs</sub>	1,000	2,500	1,500	3,000	2,500		4,000			μmho	V <sub>DS</sub> = 20 V, V <sub>GS</sub> = 0
g <sub>os</sub>		2		4			6				f = 1 kHz
C <sub>iss</sub>	15			15			15			pF	f = 1 MHz
C <sub>rss</sub>	2			2			2				
$\overline{e_n}$	8	30		8	30		8	30		$\frac{\text{nV}}{\sqrt{\text{Hz}}}$	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0
	2			2			2				f = 10 Hz
											f = 1 kHz

#### NOTES:

- Geometry is symmetrical. Unit may be operated with source and drain leads interchanged.
- Approximately doubles for every 10°C increase in T<sub>A</sub>.
- Pulse test duration = 2 ms.

NS